

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-20 (canceled)

21. (new) A Schottky diode comprising:

- a semiconductor body of a first conductance type;
- a Schottky contact which is provided on the semiconductor body;
- and two or more regions of the other conductance type located in the semiconductor body (1, 2) underneath and are at least partially adjacent to the Schottky contact (6) wherein,

- in order to initiate the injection of a starting current, each of a first set of regions of the two or more regions has a minimum distance (D) between its center of the first region and an area of the first conductance type is considerably greater than the corresponding minimum distance (d) between each of a second set of regions of the two or more regions and the area of the first conductance type.

22. (new) The Schottky diode as claimed in claim 21, wherein each of the first set of regions has a larger area than the respective areas of each of the second set of regions.

23. (new) The Schottky diode as claimed in claim 21, wherein at least one of the first set of regions and at least one of the second set of regions are at least partially cohesive.

24. (new) The Schottky diode as claimed in claim 21, wherein the two or more regions of the other conductance type are at least partially in the form of strips, and at least two regions which are in the form of strips are connected to one another via at least one of the first set of regions.
25. (new) The Schottky diode as claimed in claim 24, wherein at least one of the first set of regions has a shape that is one of the set of rectangular, square, round and oval.
26. (new) The Schottky diode as claimed in claim 21, wherein at least one of the two or more regions of the other conductance type forms an annular region disposed at an edge of the Schottky contact.
27. (new) The Schottky diode as claimed in claim 21, wherein at least one of the first set of regions is provided at an edge of the Schottky contact.
28. (new) The Schottky diode as claimed in claim 27, wherein at least one of the first set of regions has a sawtooth shape.
29. (new) The Schottky diode as claims in claim 27, where the second set of regions are incorporated in an area which is surrounded by at least one of the first set of regions.
30. (new) The Schottky diode as claimed in claim 29, wherein each of the second set of regions have a shape that is one of the set of rectangular, square and round.
31. (new) The Schottky diode as claims in claim 21, wherein the two or more regions of the other conductance type have a shape that is one of the set of square and rectangular.
32. (new) The Schottky diode as claimed in claim 24, wherein at least some of the second set of region which are in the form of strips extend in a parallel manner from at least one of the first set of regions.

33. (new) The Schottky diode as claimed in claim 21, wherein the Schottky contact has an interrupted configuration.

34. (new) The Schottky diode as claimed in claim 21, wherein the Schottky contact is constructed of titanium.

35. (new) The Schottky diode as claimed in claim 21, further comprising an opposing electrode disposed opposite of the Schottky contact, the opposing electrode constructed of nickel.

36. (new) The Schottky diode as claimed in claim 21, wherein the first conductance type is the n-conductance type.

37. (new) The Schottky diode as claimed in claim 21, wherein the semiconductor body is composed of silicon or silicon carbide.

38. (new) A Schottky diode comprising:

- a semiconductor body of a first conductance type;
- a Schottky contact which is provided on the semiconductor body (1, 2);
- and two or more regions of the other conductance type located in the semiconductor body (1, 2) underneath and are at least partially adjacent to the Schottky contact wherein,

in order to initiate the injection of a starting current, each of a first set of regions of the two or more regions has a minimum distance (D) between its center of the first region and an area of the first conductance type is considerably greater than the corresponding minimum distance (d) between each of a second set of regions of the two or more regions and the area of the first conductance type, wherein

the minimum distance (D) is chosen such that the at least one region acts as a starting area, and results in the injection of starting current.

39. (new) The Schottky diode as claimed in claim 21, where the center of at least one of the first set of regions is not exclusively located in a transitional area between an active are of the Schottky diode and an edge area.

40. (new) A Schottky diode having a semiconductor body(1, 2) of a first conductance type, having a Schottky contact (6) which is provided on the semiconductor body (1, 2), and having two or more regions (4, 5) of the other conductance type, which are located in the semiconductor body (1, 2) underneath the Schottky contact (6) and are at least partially adjacent to the Schottky contact (6),wherein in order to initiate the injection of a starting current, each of a first set of regions of the two or more regions has a minimum distance (D) between its center of the first region and an area of the first conductance type is considerably greater than the corresponding minimum distance (d) between each of a second set of regions of the two or more regions and the area of the first conductance type, and wherein

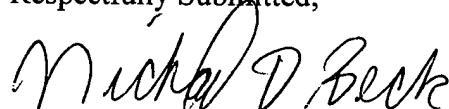
the center of at least one of the first set of regions is not exclusively located in a transitional area between an active are of the Schottky diode and an edge area.

II. Conclusion

Applicant respectfully requests entry of the amendment and favorable consideration of the application.

A prompt and favorable action on the merits is requested.

Respectfully Submitted,

A handwritten signature in black ink, appearing to read "Michael D. Beck". The signature is fluid and cursive, with the first name "Michael" and last name "Beck" being more prominent than the middle initial "D".

December 19, 2003

Michael D. Beck
Attorney for Applicants
Attorney Registration No. 32,722
Maginot, Moore & Beck
Bank One Center Tower
111 Monument Circle, Suite 3000
Indianapolis, IN 46204-5115
Telephone: (317) 638-2922